

BUK761R6-40E,118 Datasheet



DiGi Electronics Part Number Manufacturer Manufacturer Product Number

Description

Detailed Description

BUK761R6-40E,118-DG

Nexperia USA Inc.

BUK761R6-40E,118

MOSFET N-CH 40V 120A D2PAK

N-Channel 40 V 120A (Tc) 349W (Tc) Surface Mount D2PAK

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BUK761R6-40E,118	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
40 V	120A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
10V	1.6mOhm @ 25A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 1mA	145 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	11340 pF @ 25 V
FET Feature:	Power Dissipation (Max):
	349W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
D2PAK	TO-263-3, D2PAK (2 Leads + Tab), TO-263AB
Base Product Number:	
BUK761	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



BUK761R6-40E

N-channel TrenchMOS standard level FET 5 September 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404A package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static charac	teristics	1		1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	1.3	1.57	mΩ
Dynamic cha	racteristics	·		1			
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14		-	48.2	-	nC

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF4
mb	D	mounting base; connected to drain	D2PAK (SOT404A)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK761R6-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404A			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK761R6-40E	BUK761R6-40E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	1355	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	349	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
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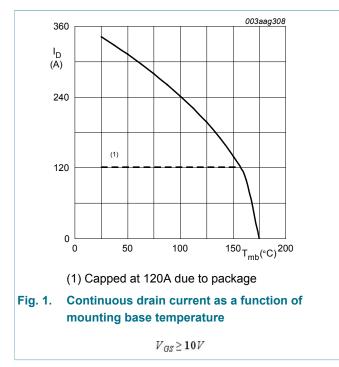
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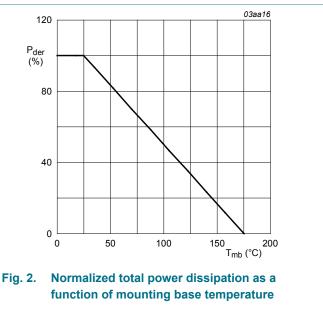
Symbol	Parameter	Conditions		Min	Мах	Unit
Source-drain	diode					_
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1355	А
Avalanche ru	ggedness	-	1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & I_{D} = 120 \; A; V_{sup} \leq 40 \; V; R_{GS} = 50 \; \Omega; \\ & V_{GS} = 10 \; V; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ & \overline{Fig. 3} \end{split}$	[2][3]	-	1008	mJ

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.

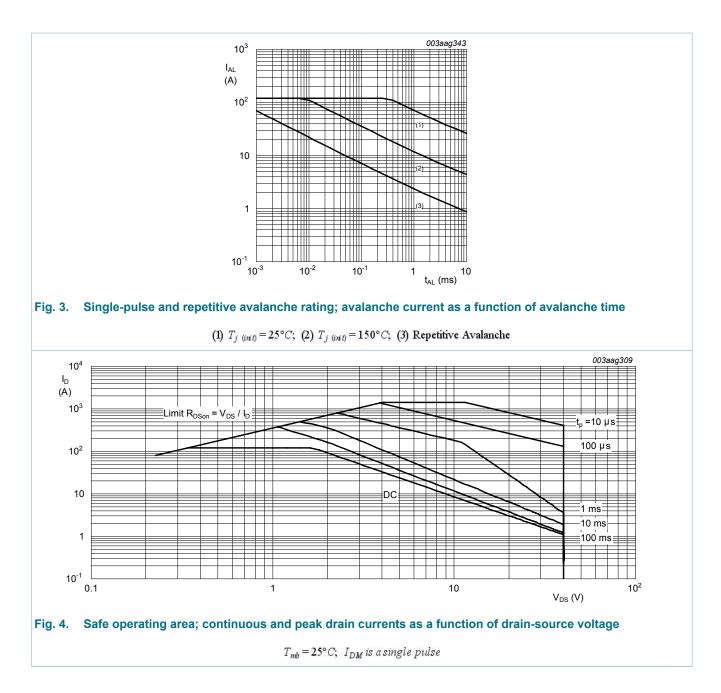




$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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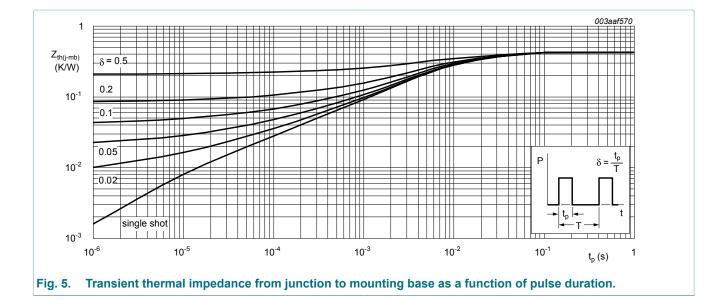
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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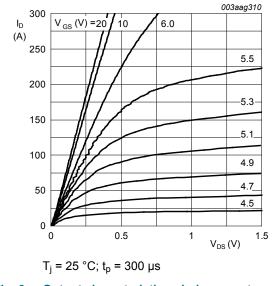
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)} gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V	
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	4.5	V	
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	1	-	-	V	
I _{DSS}	SS drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.25	2	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS} gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.3	1.57	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	3	mΩ
Dynamic ch	naracteristics	· · ·	'			
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	145	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	35.7	-	nC
Q _{GD}	gate-drain charge	1	-	48.2	-	nC

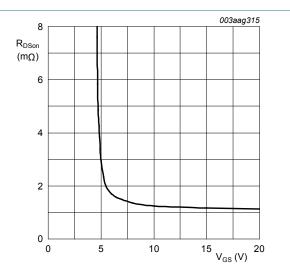
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	8500	11340	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	1620	1950	pF
C _{rss}	reverse transfer capacitance		-	985	1350	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;	-	42	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	60	-	ns
t _{d(off)}	turn-off delay time	-	-	121	-	ns
t _f	fall time		-	83	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode		· ·			,
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;	-	56	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	94	-	nC





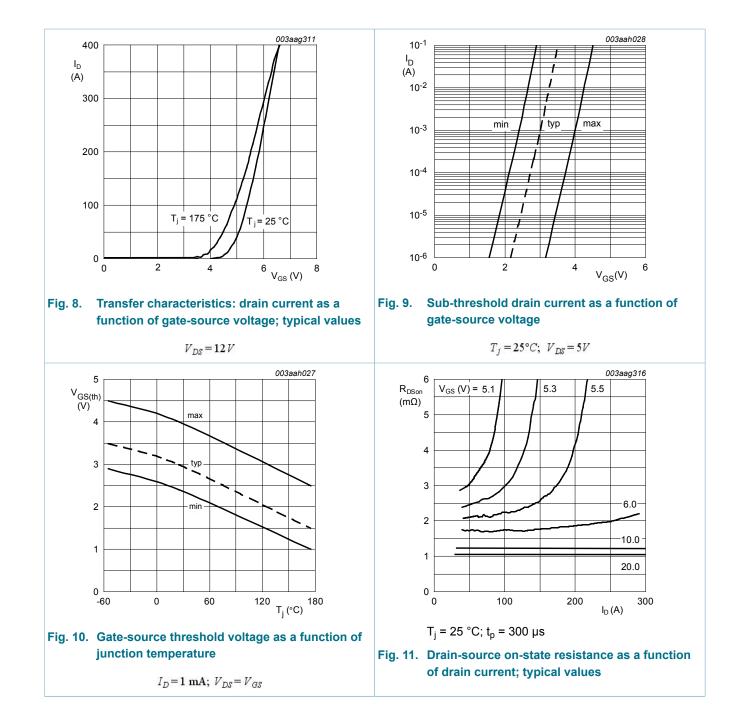




 $T_j = 25 \,^{\circ}C; I_D = 25A$

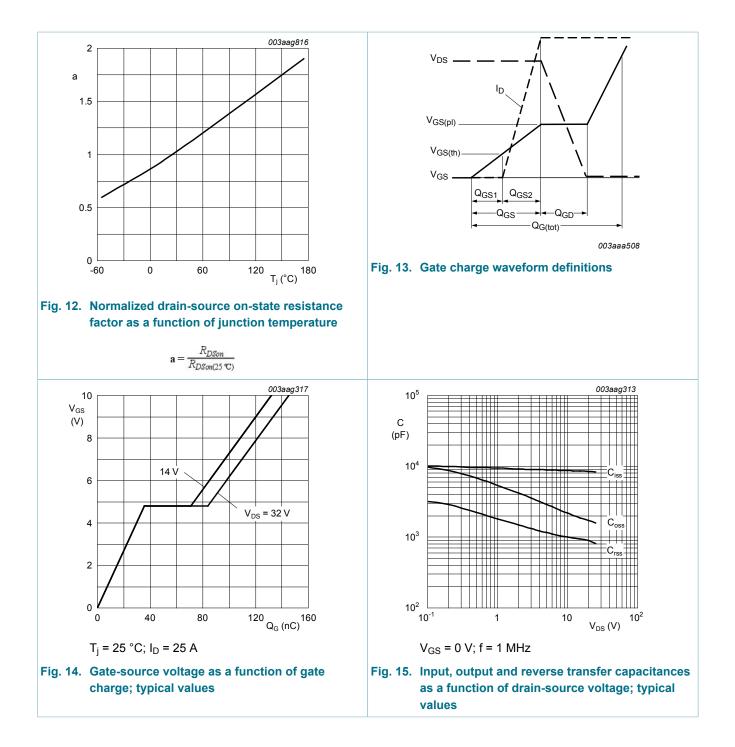
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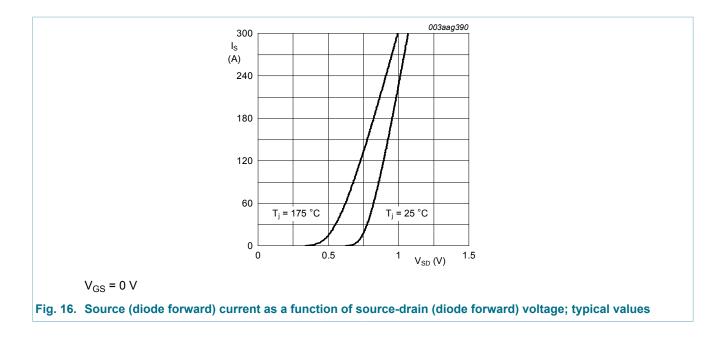
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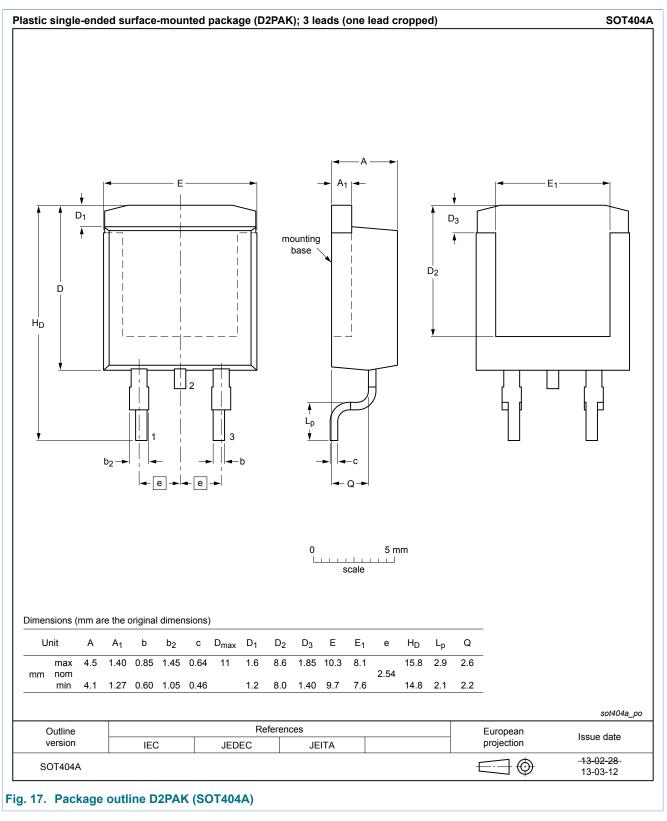


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11. Package outline



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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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 Please consult the most recently issued document before initiating or completing a design.

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